

L Number	Hits	Search Text	DB	Time stamp
1	237	plasma near2 (CVD or chemical near2 vapor near2 deposit\$5) same ion near2 beam same (si or silicon)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/10/12 11:10
3	19	plasma near2 (CVD or chemical near2 vapor near2 deposit\$5) near10 ion near2 beam near10 (si or silicon)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/10/12 11:11
2	93	plasma near2 (CVD or chemical near2 vapor near2 deposit\$5) near10 ion near2 beam same (si or silicon)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/10/12 11:13
4	93	plasma near2 (CVD or chemical near2 vapor near2 deposit\$5) near10 (si or silicon) same (ion near2 beam)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/10/12 11:37
5	50	(plasma near2 (CVD or chemical near2 vapor near2 deposit\$5) or PECVD) near10 (si or silicon) same ion near2 source	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/10/12 13:20
6	0	5795385.pn. and silane same (hydrogen or "h.sub.2")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/10/12 13:21
7	1	5795385.pn. and (hydrogen or "h.sub.2")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/10/12 13:21
8	592	(kirimura near2 hiroya or kiyoshi near2 ogata).in.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/10/12 13:24
9	26	((kirimura near2 hiroya or kiyoshi near2 ogata).in.) and (silicon or si) near2 (film or layer) same (laser)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/10/12 13:37
10	9	((kirimura near2 hiroya or kiyoshi near2 ogata).in.) and (silicon or si) near2 (film or layer) same energy near2 beam	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/10/12 13:37
-	2	laser same recrystal\$8 same (silicon or si) near10 crystal\$7 same deposit\$5 same in\$1situ	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/10/05 13:45
-	4	laser same recrystal\$8 same (silicon or si) near10 crystal\$7 same deposit\$5 same chamber	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/10/05 13:46
-	15	laser same recrystal\$8 same (silicon or si) same deposit\$5 same chamber	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/10/05 13:47
-	2	"20010032589"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/10/05 14:07

-	5	"0652308"	USPAT; US_PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US_PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US_PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US_PGPUB; EPO; JPO; DERWENT;	2004/10/05 13:52
-	9	"652308"	USPAT; US_PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US_PGPUB; EPO; JPO; DERWENT;	2004/10/05 13:56
-	41	laser same deposit\$5 near10 (si or silicon) same in\$1situ	IBM_TDB USPAT; US_PGPUB; EPO; JPO; DERWENT;	2004/10/05 13:57
-	106	single near5 (chamber or apparatus) same laser same deposit\$5	IBM_TDB USPAT; US_PGPUB; EPO; JPO; DERWENT;	2004/10/05 14:37
-	10087	laser near5 (anneal\$5 or recrystal\$8)	IBM_TDB USPAT; US_PGPUB; EPO; JPO; DERWENT;	2004/10/05 14:37
-	4493	(laser near5 (anneal\$5 or recrystal\$8)) same (si or silicon) near5 (film or layer)	IBM_TDB USPAT; US_PGPUB; EPO; JPO; DERWENT;	2004/10/05 14:37
-	290	((laser near5 (anneal\$5 or recrystal\$8)) same (si or silicon) near5 (film or layer)) and vacuum near2 chamber	IBM_TDB USPAT; US_PGPUB; EPO; JPO; DERWENT;	2004/10/05 14:38
-	24	((laser near5 (anneal\$5 or recrystal\$8)) same (si or silicon) near5 (film or layer)) same vacuum near2 chamber	IBM_TDB USPAT; US_PGPUB; EPO; JPO; DERWENT;	2004/10/05 14:45
-	25	((laser near5 (anneal\$5 or recrystal\$8)) same (si or silicon) near5 (film or layer)) same (chamber or reactor) near5 "same"	IBM_TDB USPAT; US_PGPUB; EPO; JPO; DERWENT;	2004/10/05 15:01
-	43	laser near5 (anneal\$5 or recrystal\$7) same (chamber or reactor) near5 "same"	IBM_TDB USPAT; US_PGPUB; EPO; JPO; DERWENT;	2004/10/05 15:06